

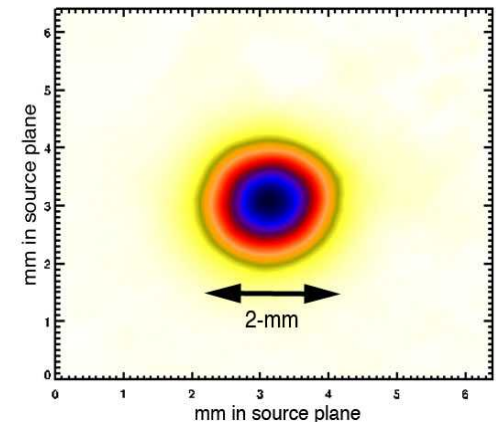
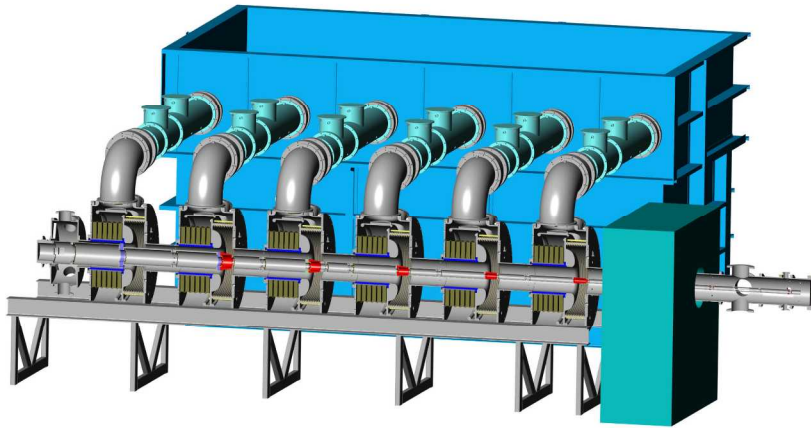
Recent Advances in Radiographic X-ray Source Development at Sandia*

SAND2008-4473P

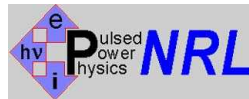
B.V. Oliver

Sandia National Laboratories, Albuquerque, NM 87185, USA

presented at the
17th Intl. Conf. on High Power Particle
Xian, China
July 7-11, 2008



*In collaboration with the Atomic Weapons Establishment U.K., Naval Research Laboratories, Los Alamos, NSTec, and Voss Scientific:



Sandia is a multiprogram laboratory operated by Sandia Corporation, a Lockheed Martin Company, for the United States Department of Energy's National Nuclear Security Administration under contract DE-AC04-94AL85000.





Acknowledgements

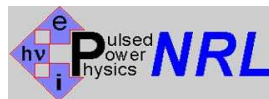
We have a large number of collaborators on pulsed-power driven radiographic diode research:



K. Hahn
M. Johnston
J. Leckbee
J. Maenchen
I. Molina
S. Cordova
D. Rovang
S. Portillo
E. Ormand

Others

E. Schamiloglu (UNM)
J. Smith (LANL)
D. Droemer (NSTec)
D. Rose (Voss)
D. Welch (Voss)
N. Bruner (Voss)



G. Cooperstein
R. Comisso
D. Hinshelwood
D. Mosher
P. Ottinger
S. Strausberg
S. Swanekamp (L-3)
J. Schumer
B. Weber
F. Young (L-3)

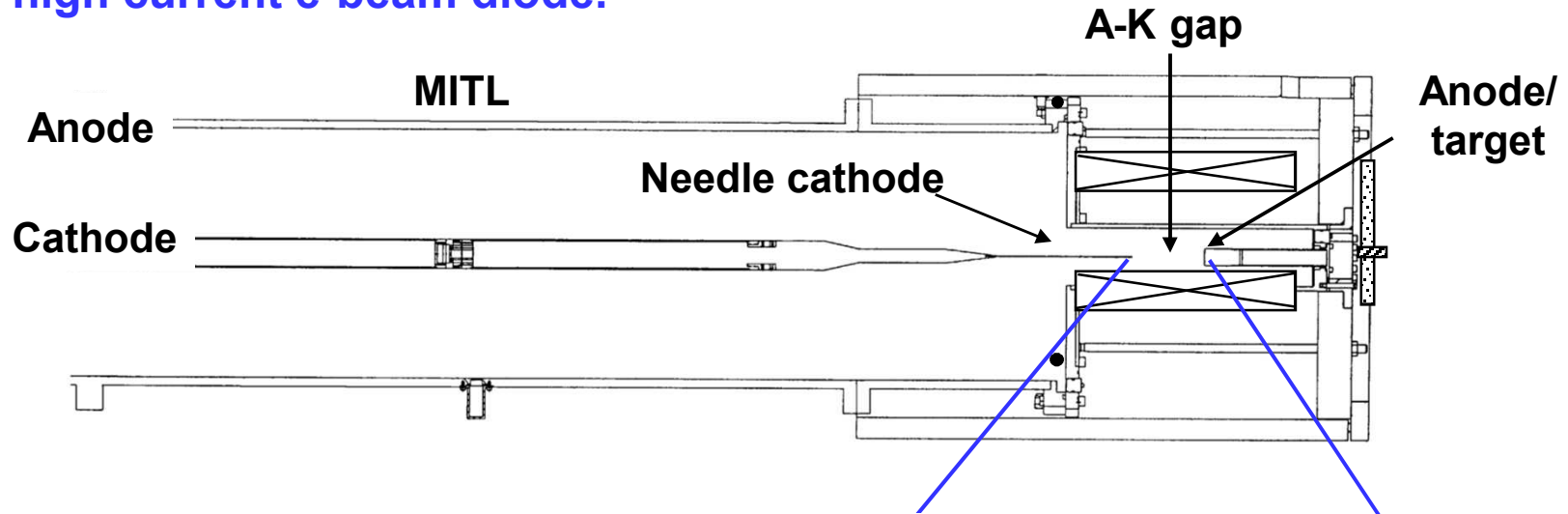
I. Smith (L-3)
D. Johnson (L-3)
V. Bailey (L-3)
P. Corcoran (L-3)



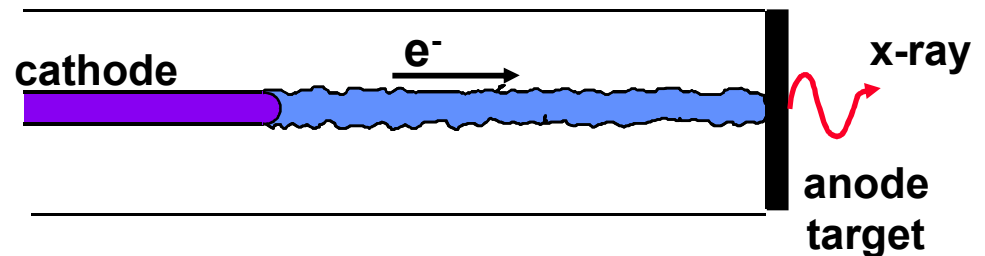
J. O'Malley
D. Short
A. Birrell
G. Cooper
J. McClean
M. Sinclair
J. Threadgold
P. Martin
A. Critchley
T. Goldsack

Inductive Voltage Adder (IVA) based e-beam driven radiography

The electron beam is created in the accelerating gap of a high current e-beam diode.



Bremsstrahlung x-rays are created when the e-beam is stopped in a high atomic number converter.



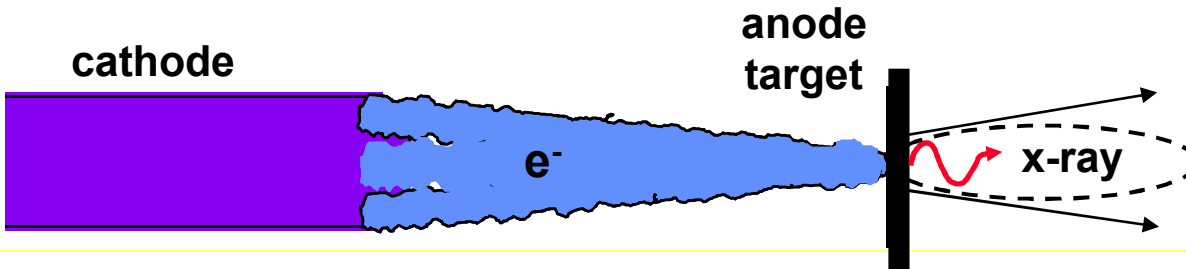
Energy = 2-10 MeV, Current = 20-150 kA, Pulse length = 50-100ns

Some General Beam/Radiation Principles

Radiation dose/flux:

$$\propto \int dt I_b V^\alpha, \quad 1 < \alpha < 3$$

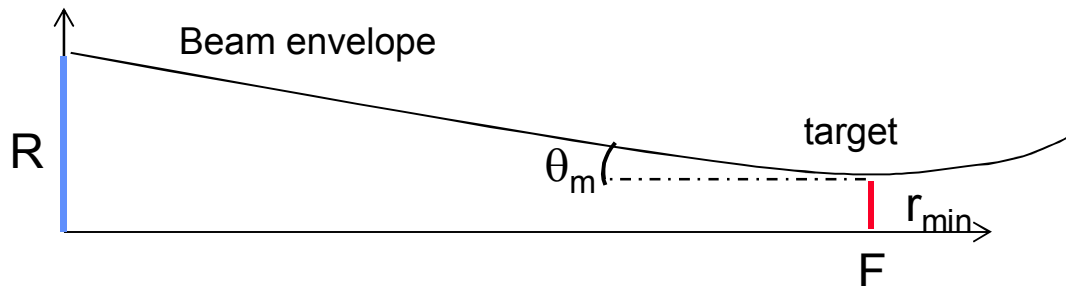
related to the beam current I and voltage V .



x-rays are forward directed within an angle $\propto 1/\gamma$. α is dependent on beam angles of incidence and temperature.

Radiation spot size:

equivalent to the beam spot on target.



$$r_{\min} \cong \theta_\mu F, \quad \theta_m \cong R / F$$

$$\theta_\mu = \frac{1}{\sqrt{\pi}} \frac{\varepsilon}{R}$$

Spots are limited by beam emittance/micro-divergence



Optimization of radiographic performance

A figure of merit (FOM) for the diode radiographic utility is quantified by the photon intensity, defined as:

$$\text{FOM} = \text{Dose/spot}^2 \quad \text{rads@m/mm}^2$$

To increase the FOM one must either decrease spot, increase dose or both.

Smaller spots are achieved by:

- increasing beam macro-angle θ_m at target
- decreasing beam emittance/micro-divergence ε, θ_μ

Larger dose is achieved by:

- decreasing beam macro-angle θ_m at target
- increasing beam energy and or current (V, I)

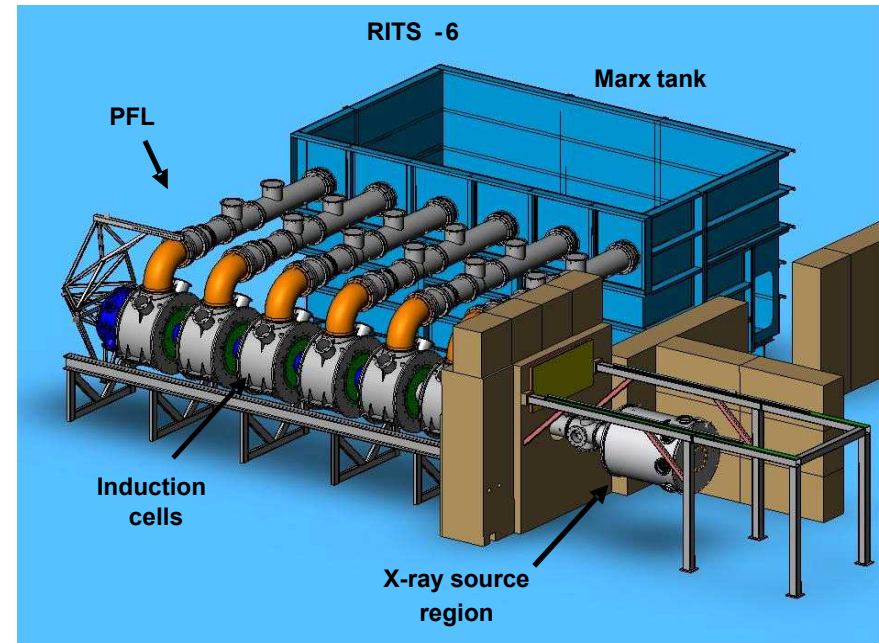
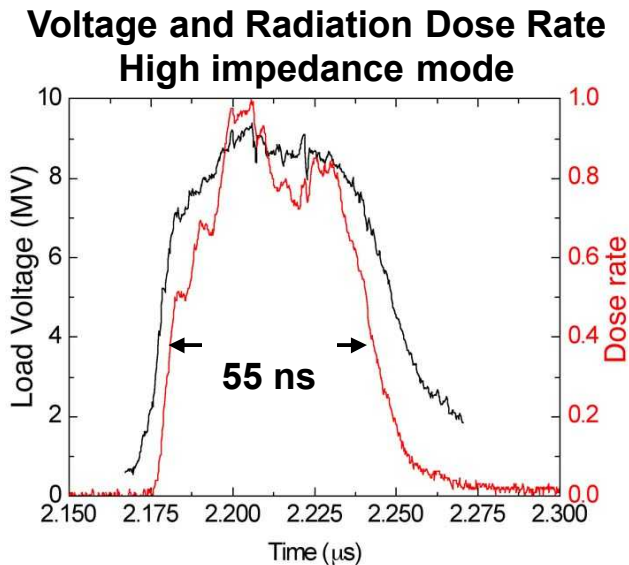


Conflicting requirements

Experiments are fielded on the Radiographic Integrated Test Stand RITS-6

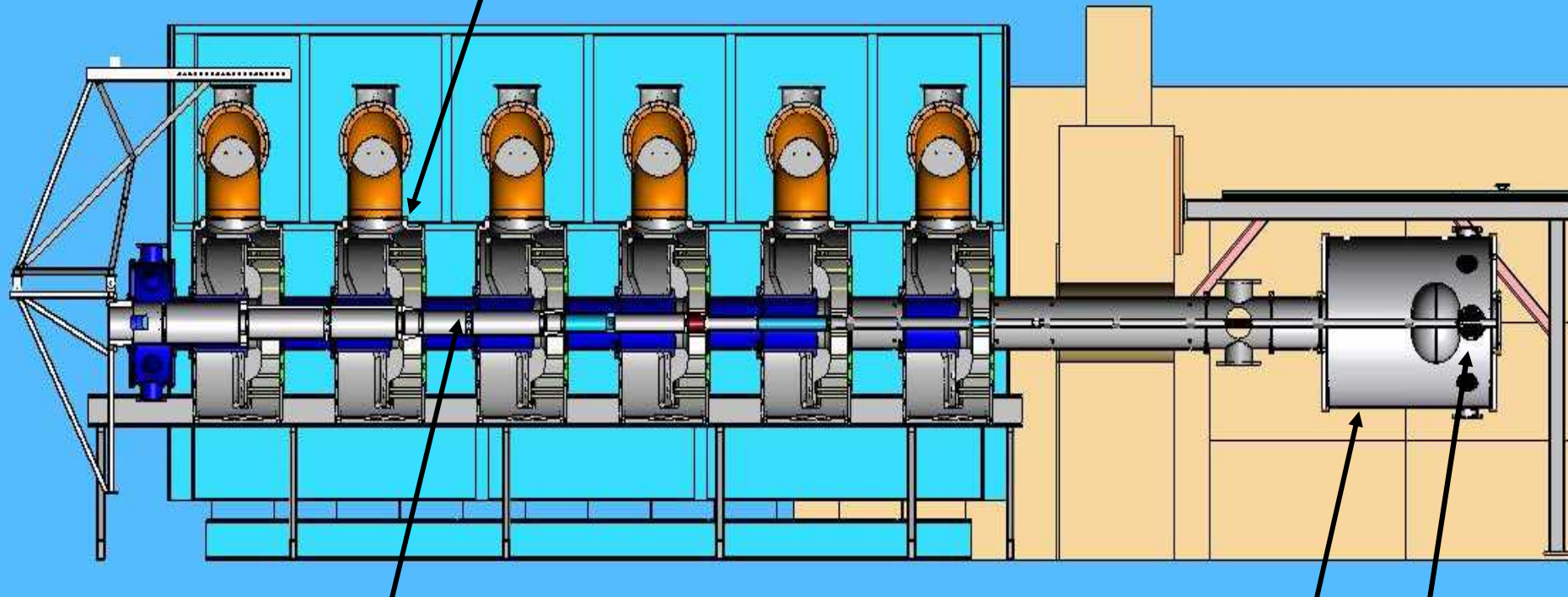
E-beam driven x-ray radiography test stand based on Induction Voltage Adder (IVA) technology

Flexible accelerator producing:
4.5-11 MV, 125-190 kA, 70 ns pulse.



RITS-6 Cross-section and MITL

Single-point feed induction cells



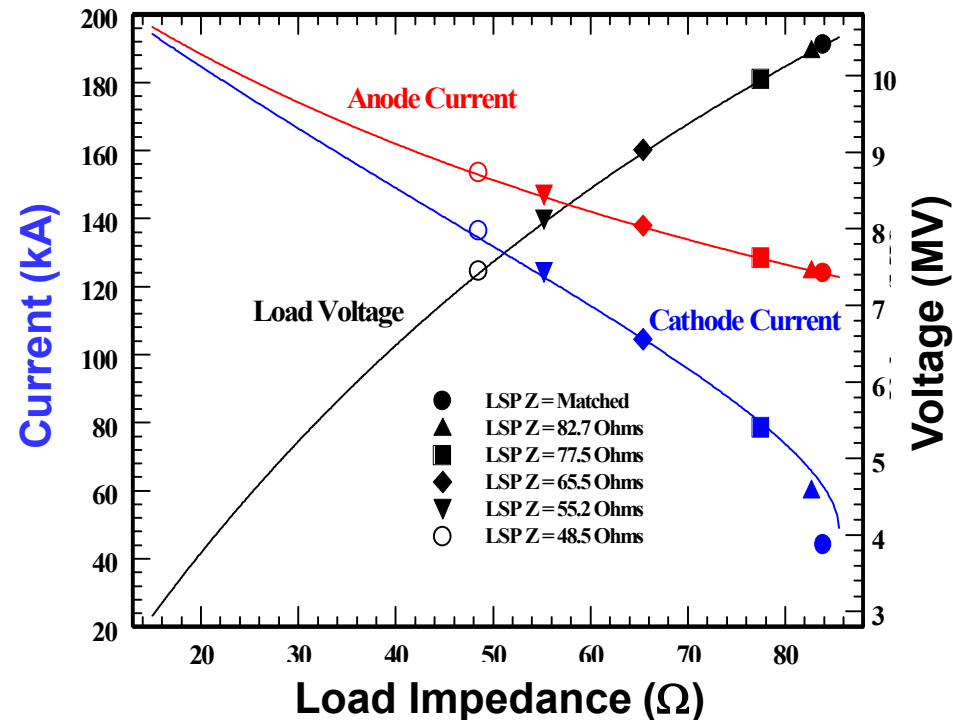
MITL impedance = $84 \, \Omega$

Dustbin

Diode

RITS-6 is a flexible accelerator architecture for driving high voltage sources.

RITS-6 MITL Operating Points



$$\text{MITL Load impedance } Z_L = V/I_A$$
$$\text{Diode impedance } Z_D = V/I_C$$

Dose $\sim IV^\alpha$, $1 < \alpha < 3$: we can increase dose by either increasing current, voltage or both

Non-linear MITL impedance $V=IZ(V)$ enables efficient drive for a variety of diode impedances. Can obtain 300% increase in diode current for only 30% decrease in voltage!

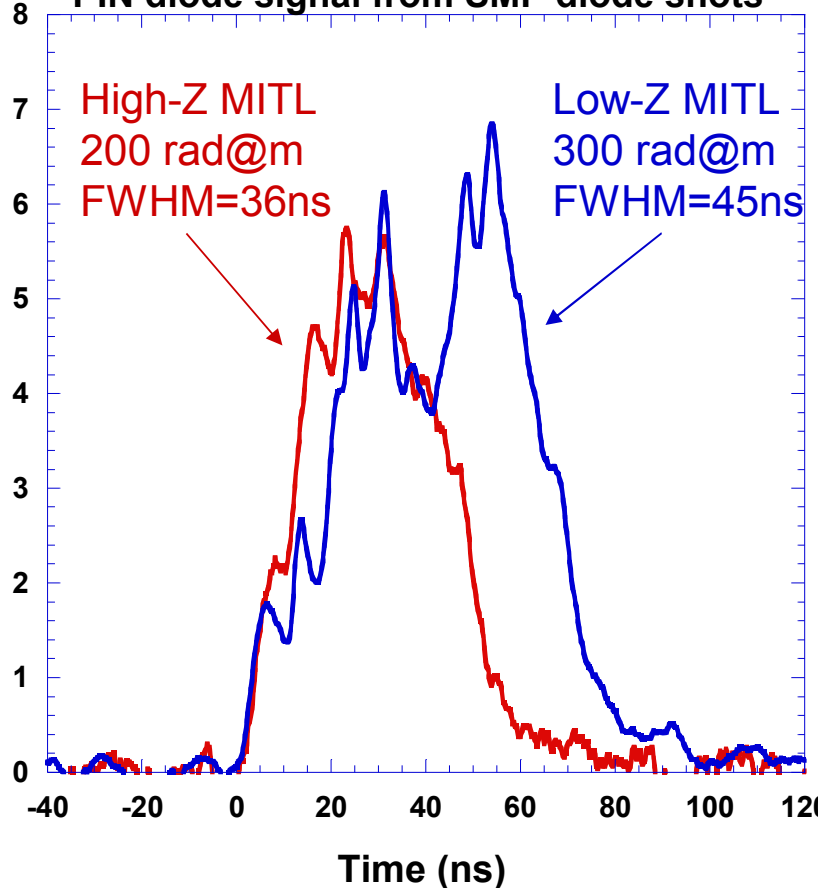
We can also use different MITL's to enhance power coupling

Minor changes to accelerator architecture increase power coupling to source

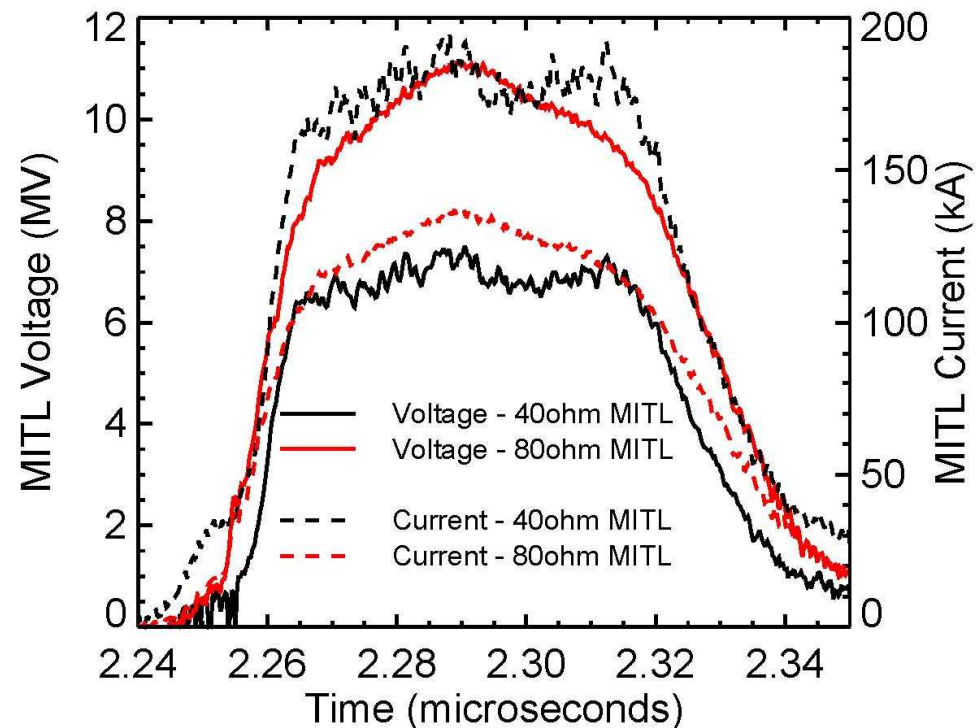
Designed a 42 Ohm MITL (vs. 82 Ohm) to thread the center of accelerator



PIN diode signal from SMP diode shots



Low impedance MITL used to couple power to low impedance sources

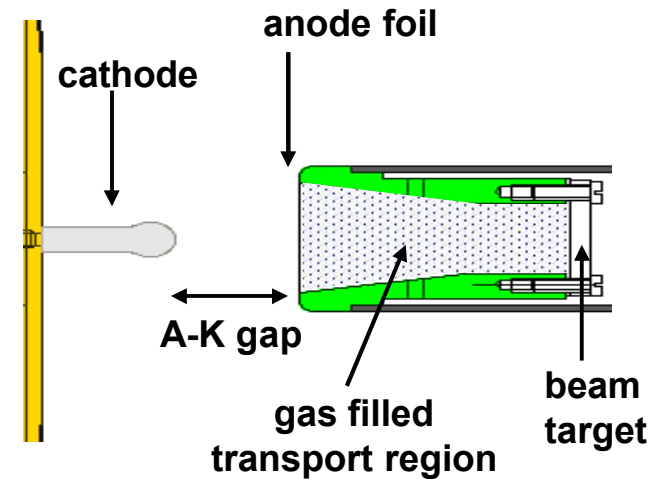


High Impedance Diodes (~200+ Ohms)

$\text{Dose} \propto IV^{2.65}$

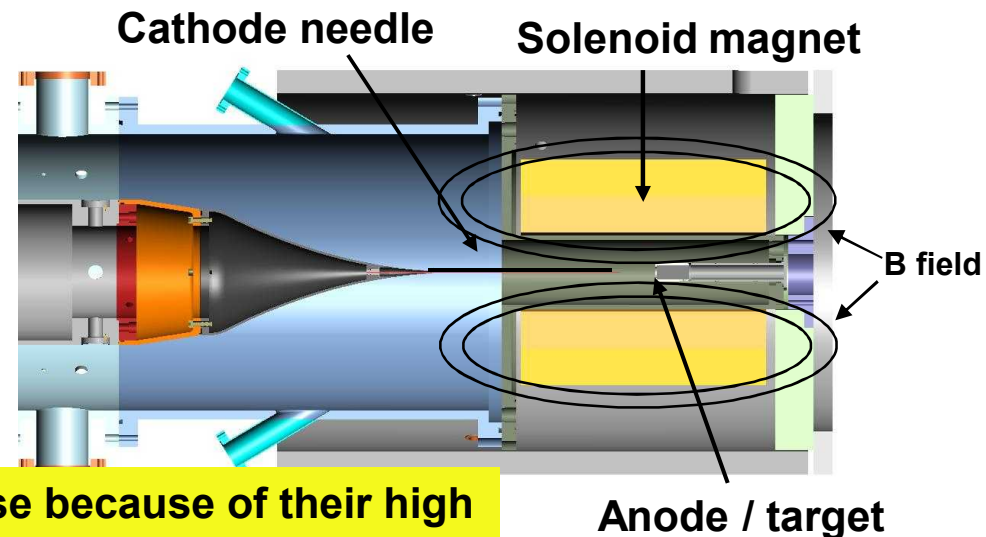
Paraxial Diode:

e-beam accelerated in vacuum A-K gap and transported to the target in gas.



Immersed B_z :

e-beam accelerated in vacuum and transported directly to anode/target. Beam is confined by strong 40T B_z magnetic field.



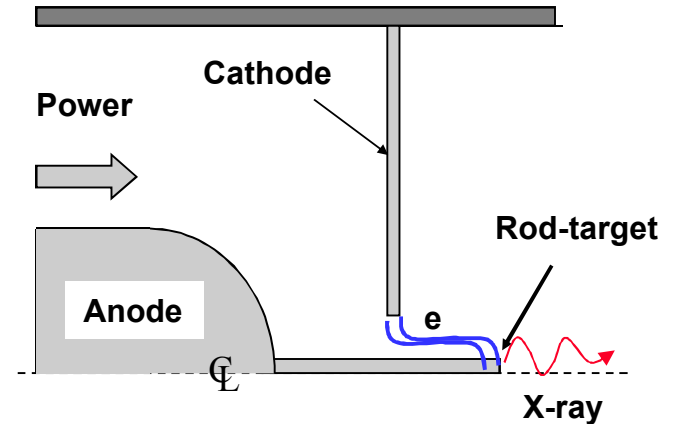
These diodes produce high radiation dose because of their high operating voltage and ~ normal incidence on target!

Low Impedance Diodes (~ 50 Ohms)

Dose $\propto IV^{1.2-2}$

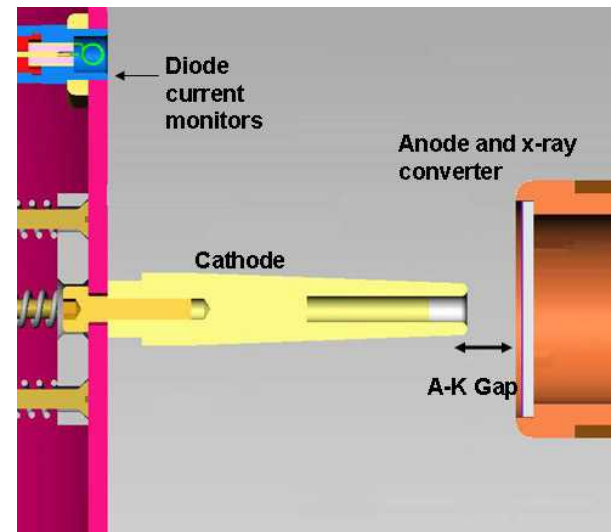
Rod-Pinch:

Bi-polar diode (e⁺ions). e-beam is self-field insulated and propagates to tip of anode rod/target.



Self-Magnetic Pinch:

Bi-polar diode (e⁺ions). e-beam is pinched onto anode/target by self-magnetic B_θ field.



These diodes produce small spots but less radiation dose because of their high average angle of incidence on target!

Paraxial diode: beam propagation in overdense gas $n_b/n_g \ll 1$. Gas-cell acts as a $\frac{1}{4}$ betatron focusing lens¹

Gas breakdown sufficient for complete charge neutralization but incomplete current neutralization.

$$\frac{d^2 r_b}{dz^2} \cong -\frac{1}{r_b} \frac{2I_{\text{net}}}{I_A} + \frac{\varepsilon^2}{r_b^3}, \quad I_{\text{net}} = I_b + I_{\text{plasma}}$$

For $\varepsilon^2 \ll 2R^2 I_{\text{net}}/I_A$

$$F \cong \frac{R}{2} \sqrt{\frac{\pi I_A}{I_{\text{net}}}}, \quad I_A = 17\gamma\beta \text{ (kA)}$$

$$\propto \sqrt{\frac{\gamma}{I_{\text{net}}}}$$

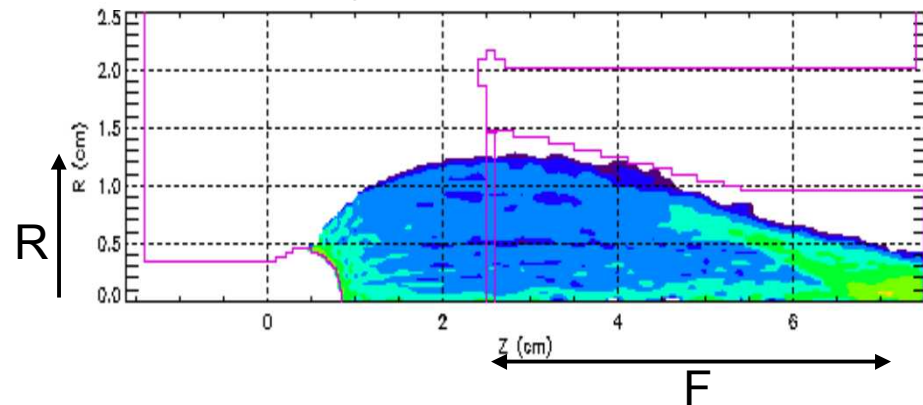
Net current (beam + plasma) $I_{\text{net}} = crB_\theta/2$

$$\frac{\partial B}{\partial t} = -\nabla \times \frac{c}{4\pi n_e} \left(\nabla \times B - \frac{4\pi}{c} j_b \right) \times B + \nabla \times \frac{c^2}{4\pi\sigma} \left(\nabla \times B - \frac{4\pi}{c} j_b \right)$$

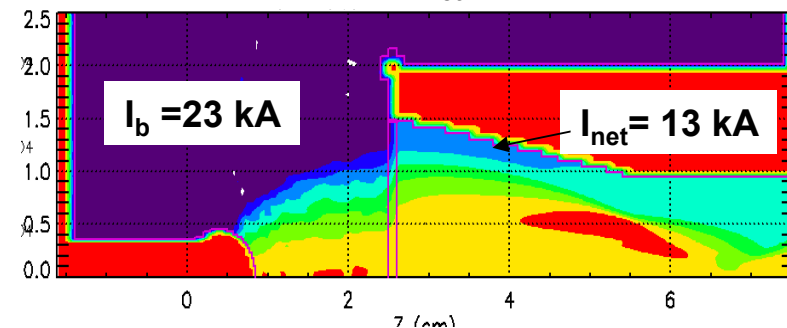
Hall current advection

Resistive diffusion

Beam density contours from Lsp simulations

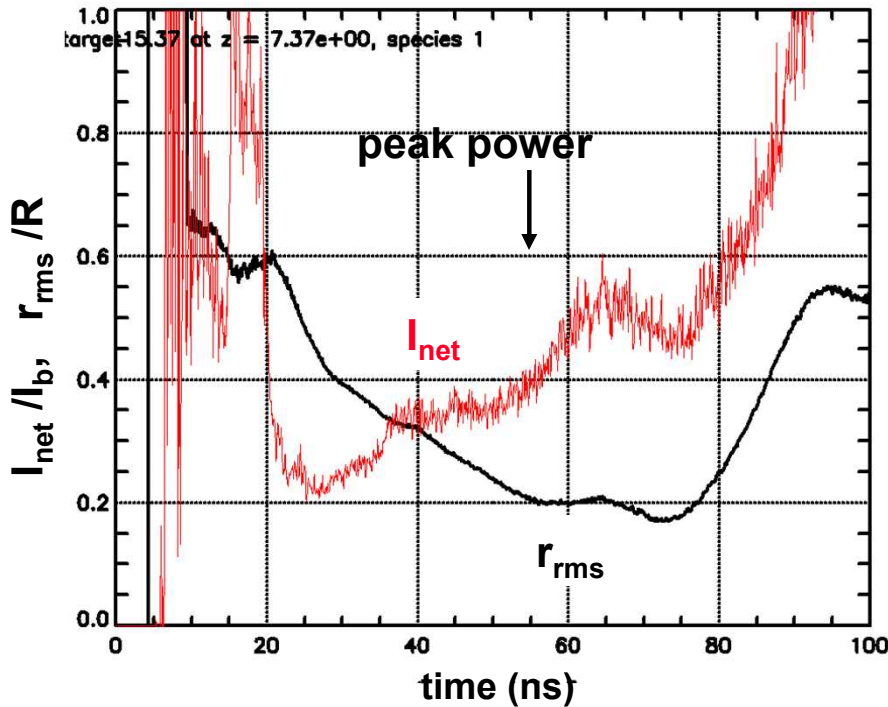


Contours of I_{net}



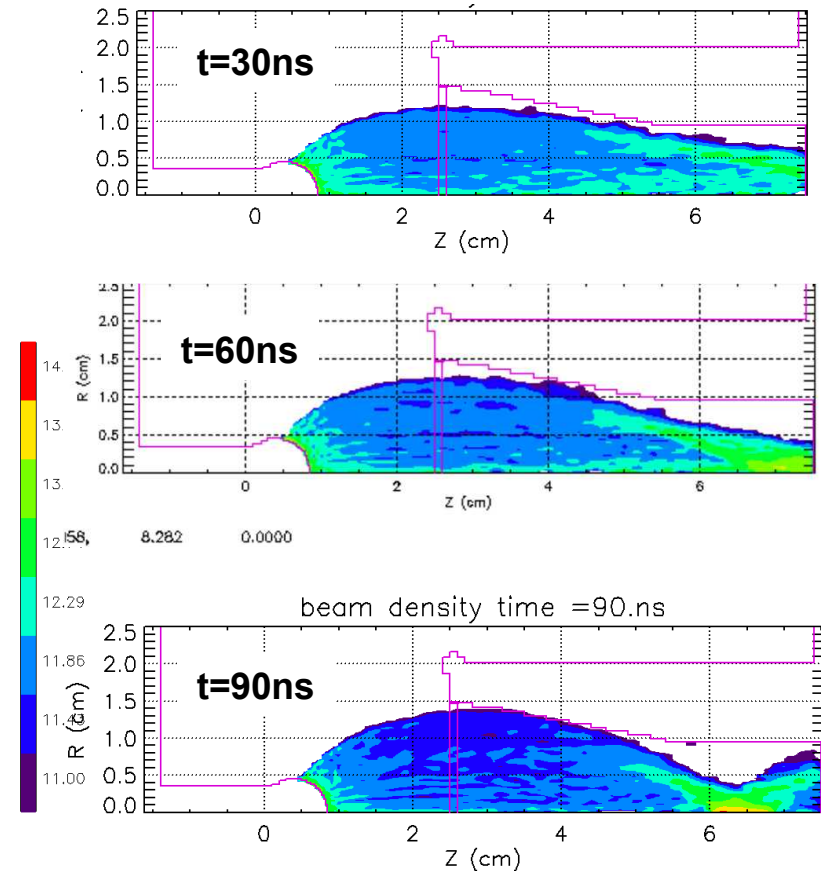
Time dependence of I_{net} causes a sweeping focus!

$$F(t) \cong \frac{R}{2} \sqrt{\frac{\pi I_A}{I_{\text{net}}(t)}}$$



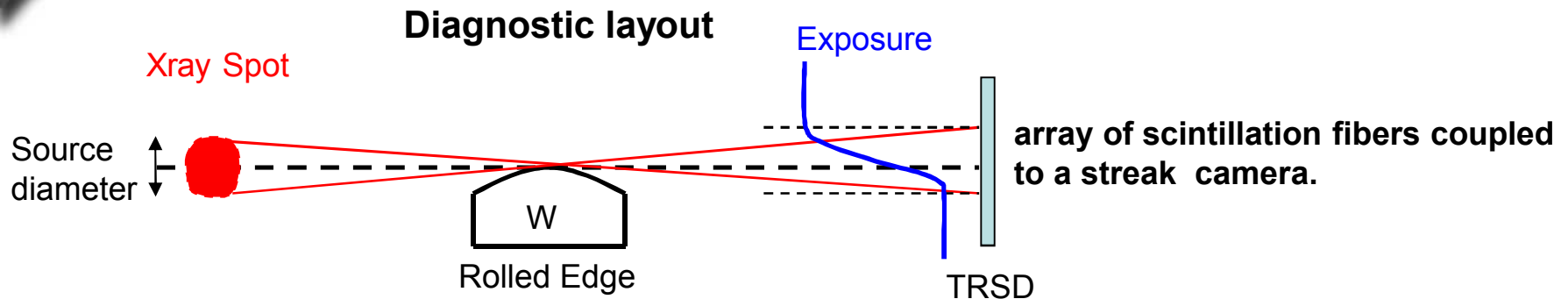
Beam rms radius and I_{net} vs time. At peak power, $I_{\text{net}} = 9 \text{ kA}$, $r_{\text{rms}} = 0.2 \text{ cm}$

Contours of beam density



Focal sweeping is a primary contributor to larger than desired time integrated spots.

Time-resolved x-ray spot diagnostic measures beam sweep on paraxial diodes



The baseline AWE x-ray source is being improved

Hybrid 3D simulations

Time resolved spot diagnostic

Spectroscopy for plasma diagnostics

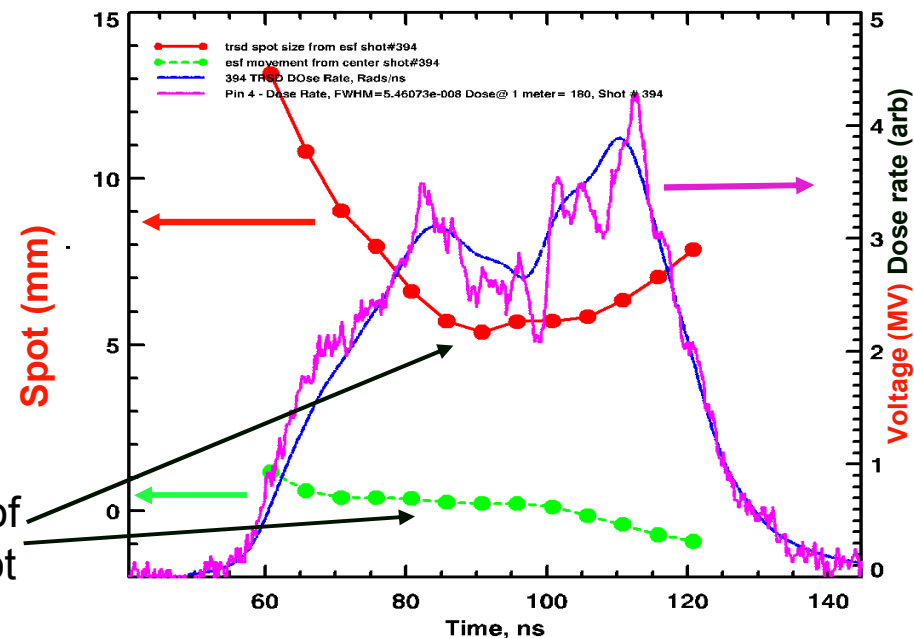
Expect to decrease the spot by a factor 2.

11 MeV Paraxial source on RITS

500 rads @ 1m from a

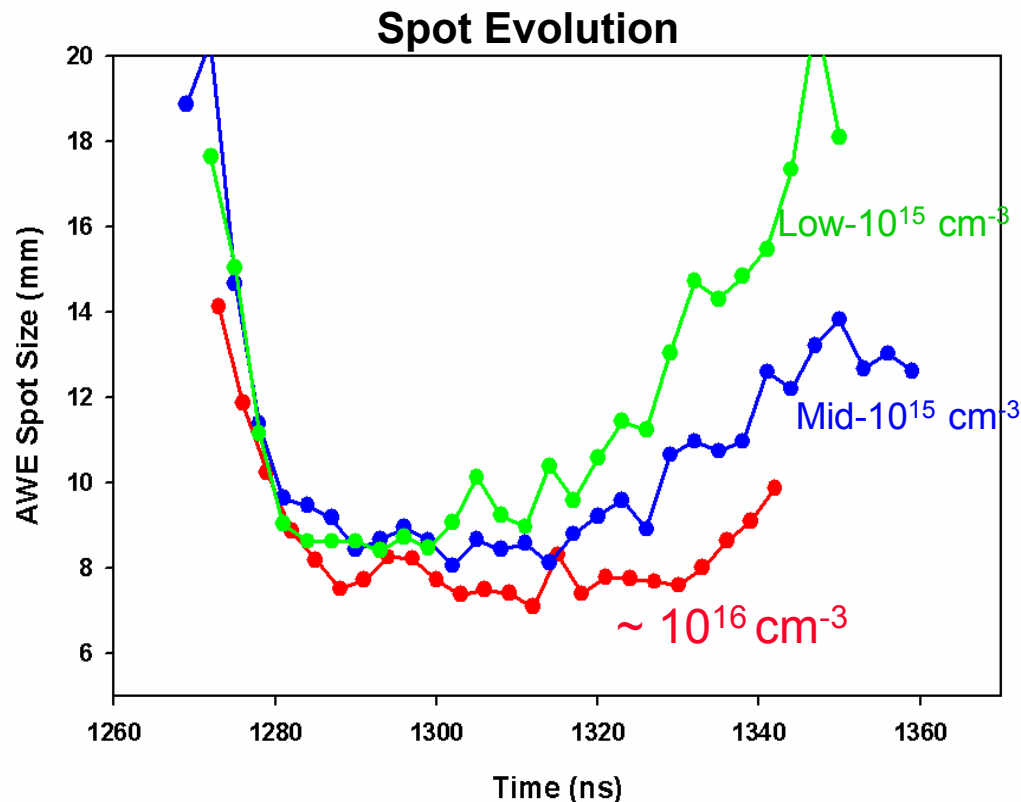
7.0 mm (0-100% AWE) spot

First measurements of
beam sweep and spot
wander



Demonstrated Plasma-filled focusing cell controls time dependent spot growth

Theory and simulations¹ suggest replacing gas-filled transport cell with a highly pre-ionized plasma limits beam sweep. Confirmed on RITS Accelerator



see K. Hahn² et al. poster

1. D. Welch, D.V. Rose, B.V. Oliver et al, Phys. Plasmas, **11**, 2004

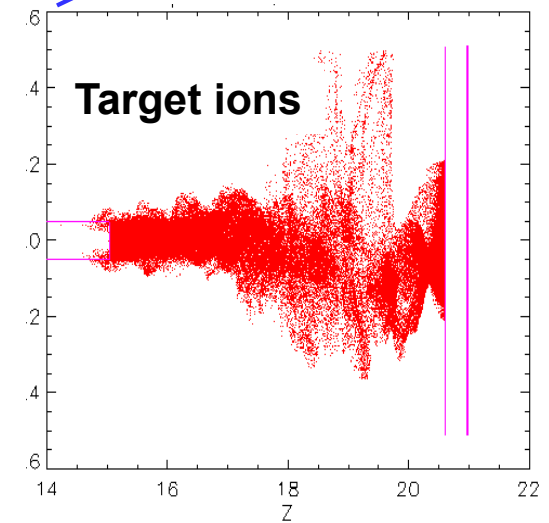
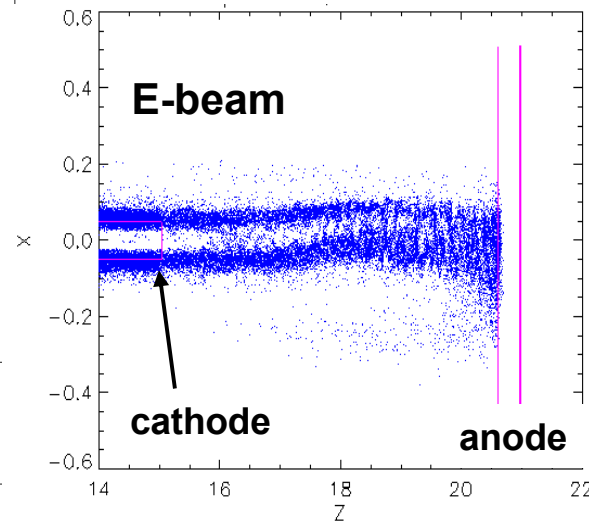
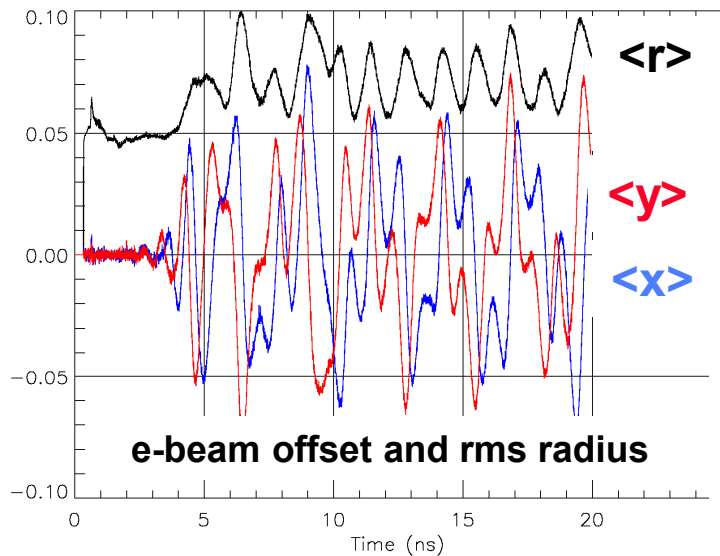
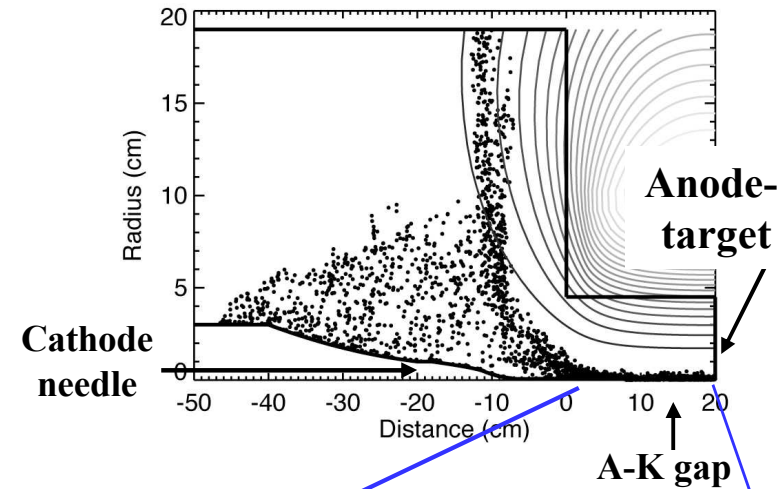
2. K. Hahn, PhD thesis, Univ. of New Mexico, 2006

The ion-hose instability limits spot-size in immersed-B_z diodes

Immersed-B¹: High dose production because beam incidence angle $\theta_m \sim 0$

spot: spot is determined by ion-hose saturation amplitude

$$\langle r_{\text{sat}} \rangle \approx \frac{c}{\Omega_e} \sqrt{2\gamma \frac{I_b}{I_A}}$$

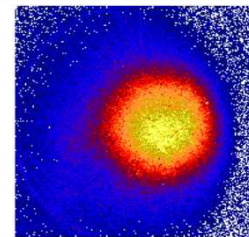
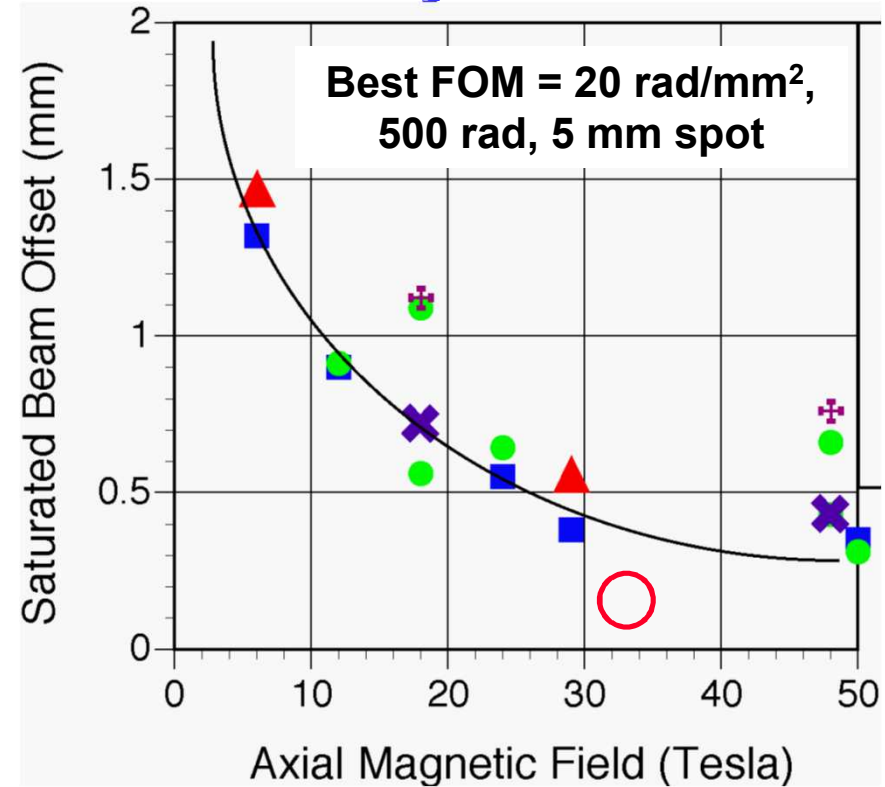
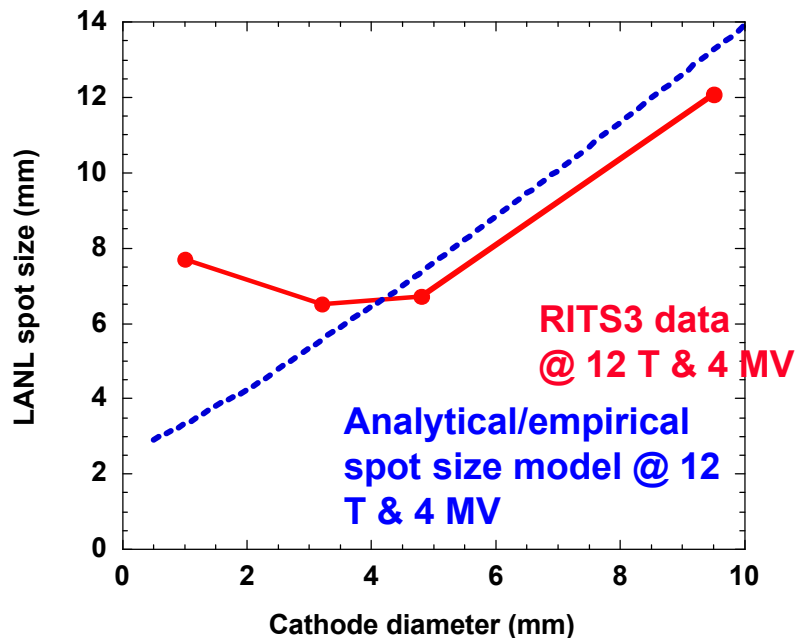


3-D PIC simulations of immersed-B diode electron and ion dynamics

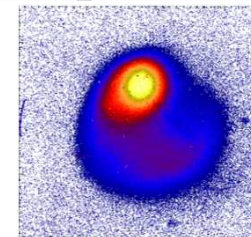
Nonlinear saturation of ion-hose $\propto 1/B_z$. But small spots influenced by ions.

Radiographic spot size decreases as $\sim 1/B$!.....up to some critical spot size!¹. Time of flight suggests ion interactions not plasma interactions.

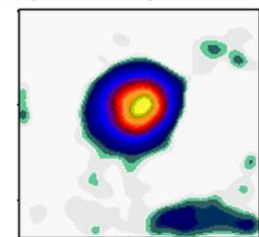
Scaling is not reproduced for small spots!



6 Tesla



29 Tesla



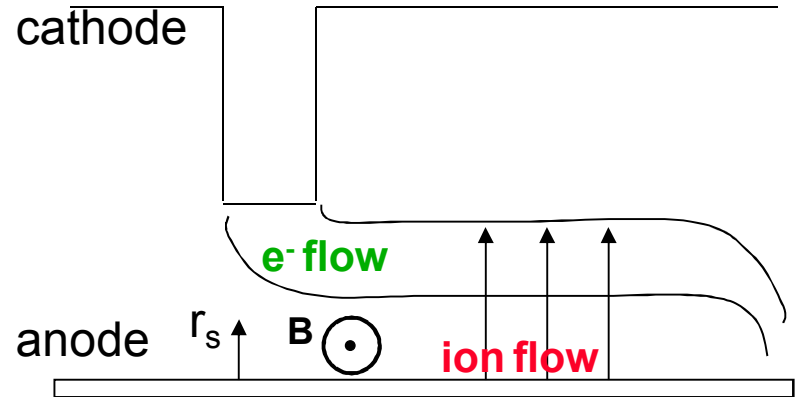
50 Tesla

Spot data courtesy of J. Maenchen²

1. D.C. Rovang et al., Phys. Plasmas **14**, 113107 (2007)
2. J. Maenchen, et al. Proc. IEEE Trans. **92**, 1021, (2004)

The Rod-Pinch is a self-magnetically insulated diode that provides small spots

rod-pinch diode



Operation is described by self-insulated flow theory with the inclusion of ions^{1,2}.

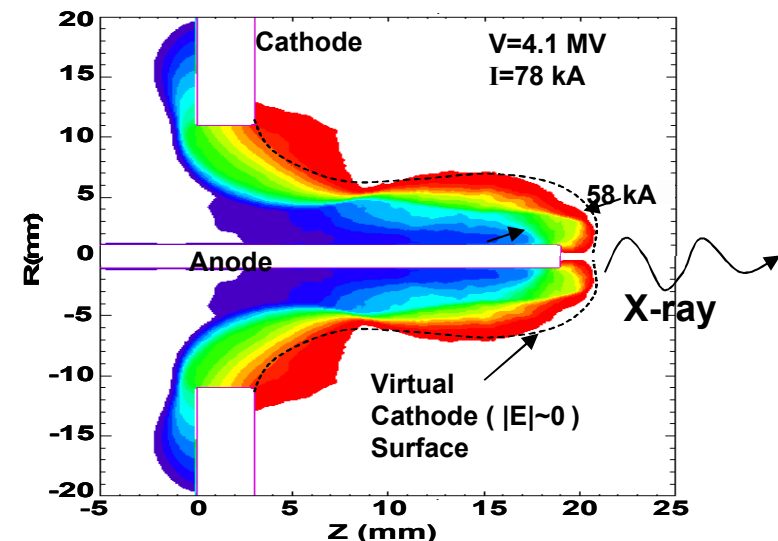
Spot determined by rod diameter

Diode current well modeled by critical current formulation:

$$I = \alpha I_{crit}, \quad 2.0 < \alpha < 2.6$$

$$I_{crit} = 8.5 \frac{\sqrt{\gamma^2 - 1}}{\ln(r_c / r_a)} \text{ kA}, \quad \gamma = 1 + eV/mc^2$$

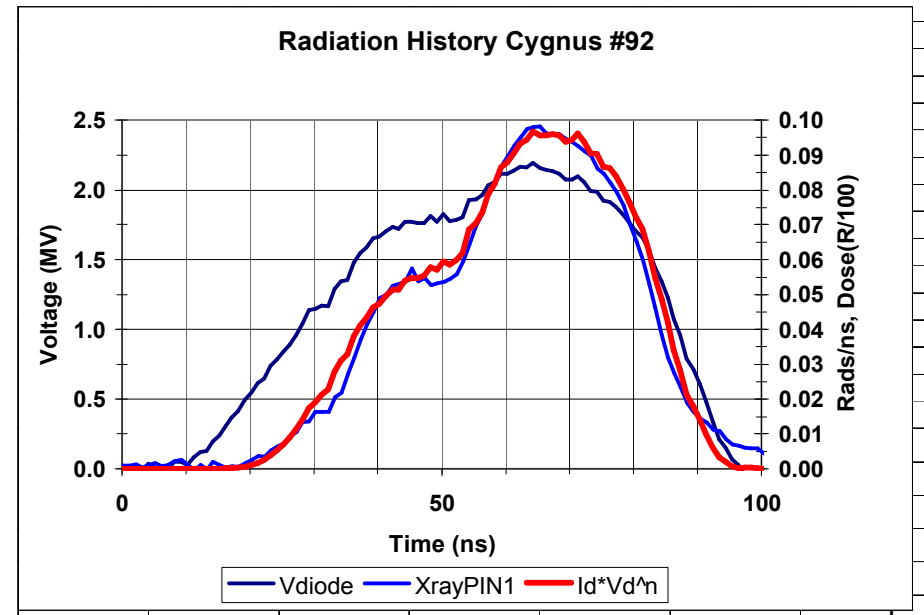
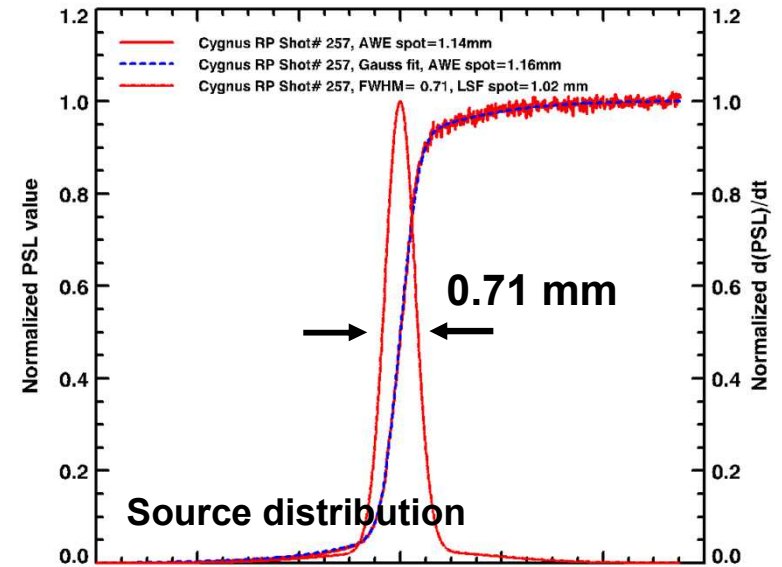
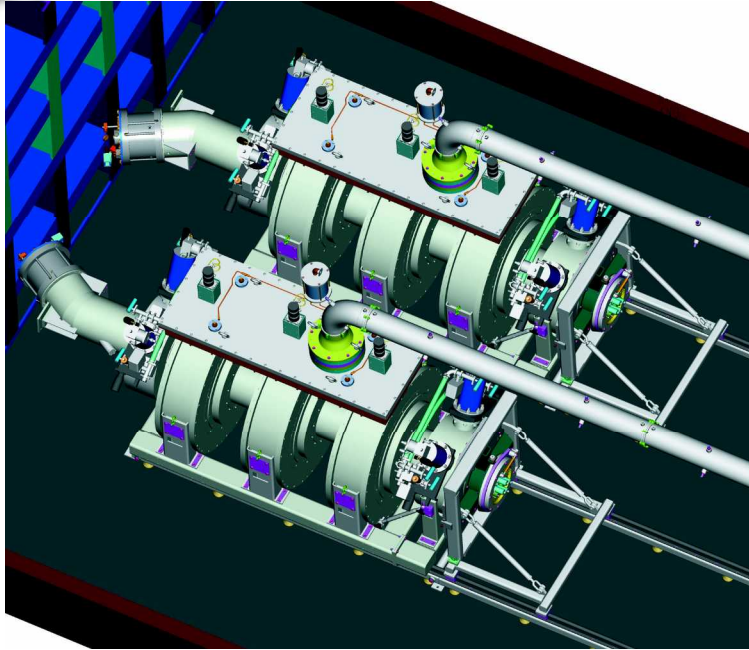
Normal Rod pinch diode



1. G. Cooperstein et al. Phys. Plasmas, **8**, 4618 (2001)
2. B.V. Oliver et al. Phys. Plasmas, **11**, (2004);

Fig. courtesy of S. Swaneekamp, NRL

Cygnus is a dual axis IVA-driven high resolution radiographic system



- Provides dual axis radiographs at NTS
- Each 2.2 MV axis produces a $> 4 \text{ rad@m}$, 1.1mm spot from a rod-pinch x-ray source.

Alternative source development for the future: Negative Polarity Rod-Pinch

Dose at 0° scales weakly with voltage¹

$$D(\text{rad}) \propto \int I_e V^{1.25} dt$$

Dose at 180° in backwards direction is maximized²

$$D(\text{rad}) \propto \int I_e V^{2.22} dt$$

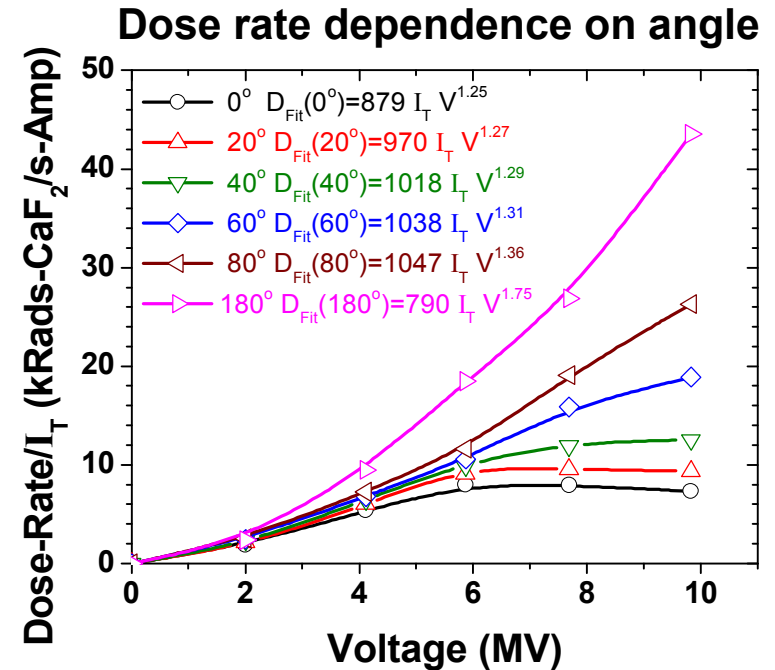
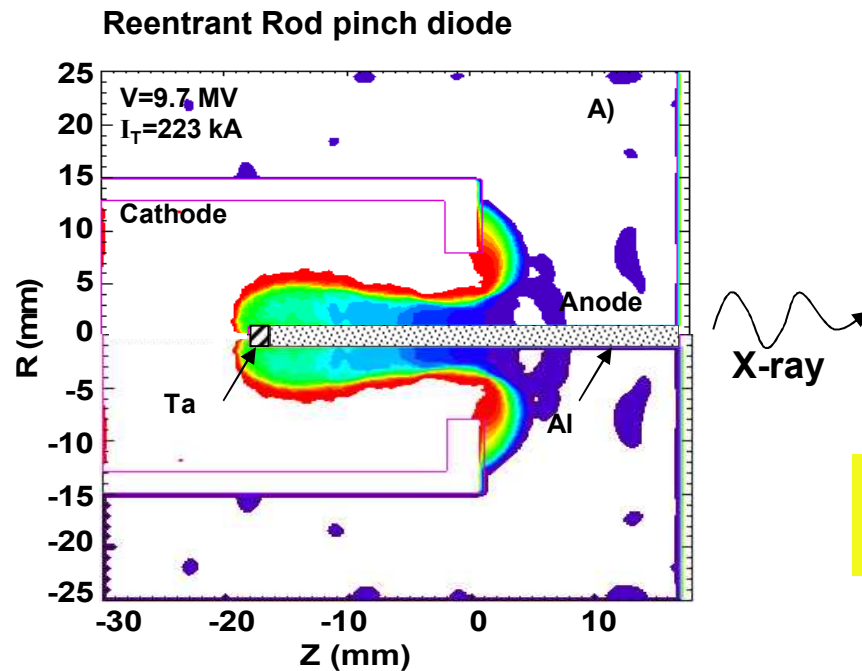


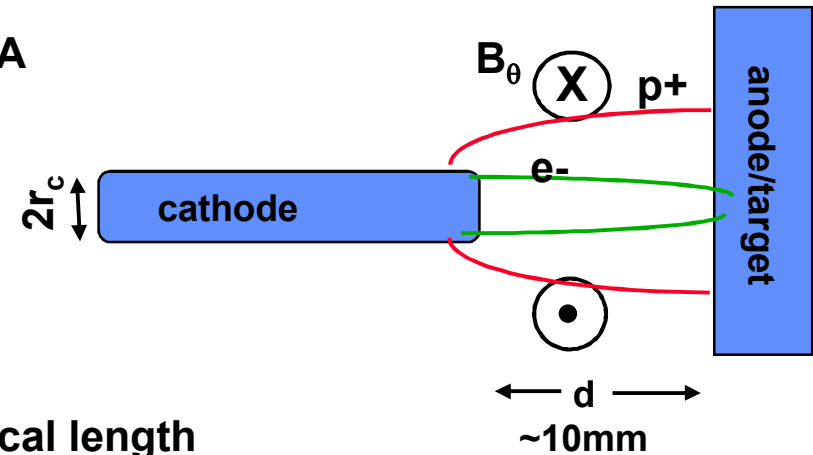
Fig. courtesy of S. Swanekamp, NRL

Should be capable of producing > 150 rad
with < 2 mm spots, FOM > 35 rad/mm²

1. D.V. Rose et al. JAP, **91**, 3328 (2002)
2. S.B Swanekamp, G. Cooperstein, J.W Schumer et al. IEEE Trans. Plasma Sci. **32**, 2004 (2004)

Self-Magnetic pinch diode acts similar to a 1/4 betatron focusing cell, but in vacuum!

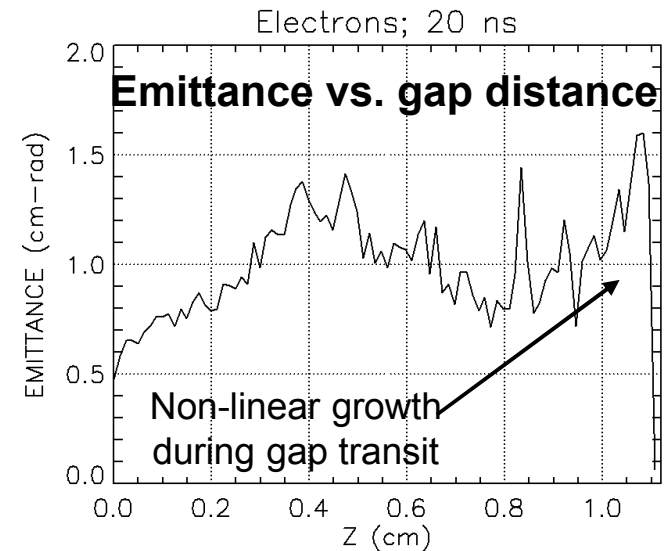
Relativistic Bi-polar diode. High current $I_b \sim 150$ kA



Self-magnetic B_θ pinches the beam on target. Focal length function of total current. Spot determined by emittance which is driven by non-linear field structure

$$F \cong \frac{r_c}{2} \sqrt{\frac{\pi I_A}{I_b}}, \quad \sim 14 \text{ mm}$$

$$\text{spot} \cong 2.4 \frac{1}{\sqrt{\pi}} \frac{\varepsilon}{r_c} F \quad \sim 2.5 \text{ mm}$$

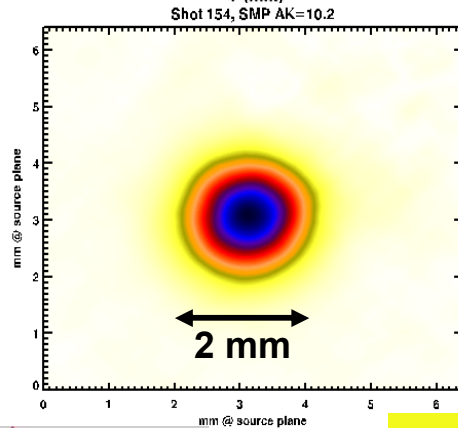
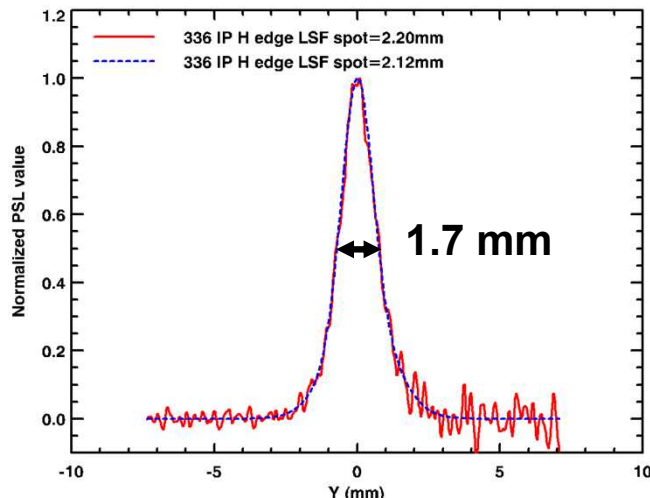


It is not influenced by ion-hose instability because the A-K gap is too small for growth.

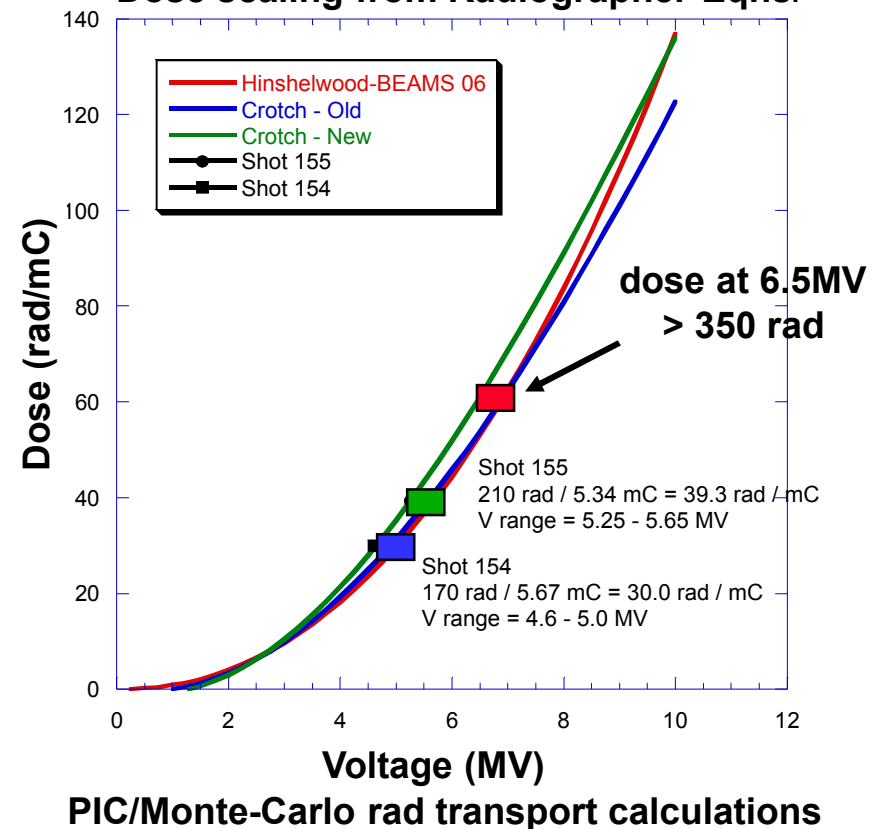
Self-pinch diode is one of our brightest sources!

SNL, AWE, NRL team have demonstrated 350+ rads from a 1.7-mm FWHM source distribution on RITS-6 Accelerator with 6.5 MeV endpoint energy.

Measured x-ray source spot



Dose scaling from Radiographer Eqns.



Demonstrated brightness > 50 rad/mm²

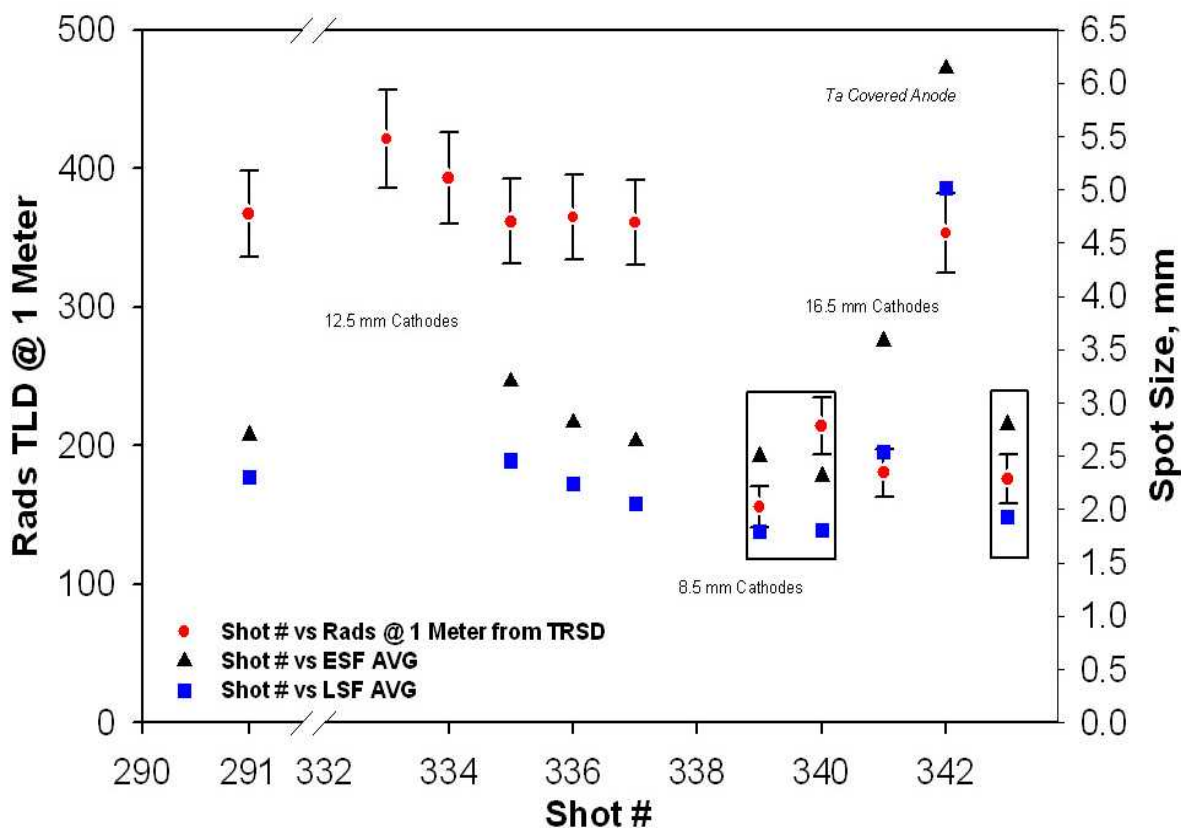
Self-pinch diode geometric changes can produce smaller spot at reduced dose.

AWE definition spot = $2.3 \text{ mm} \pm 0.2 \text{ mm}$

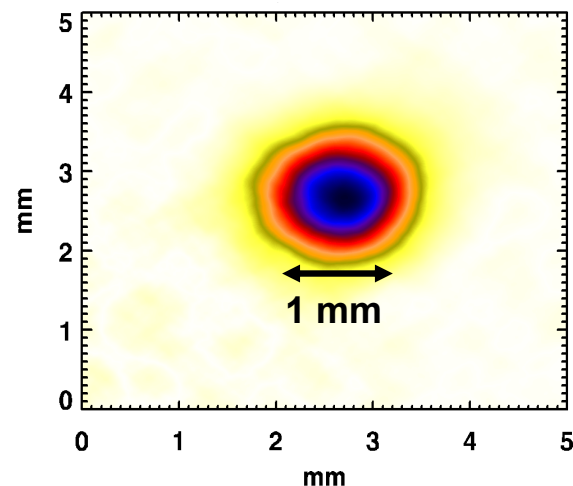
A LLNL definition ($1.44 \times \text{fwhm LSF}$) = $1.75 \pm 0.1 \text{ mm}$

Implies a peaked core (non Gaussian) spot.

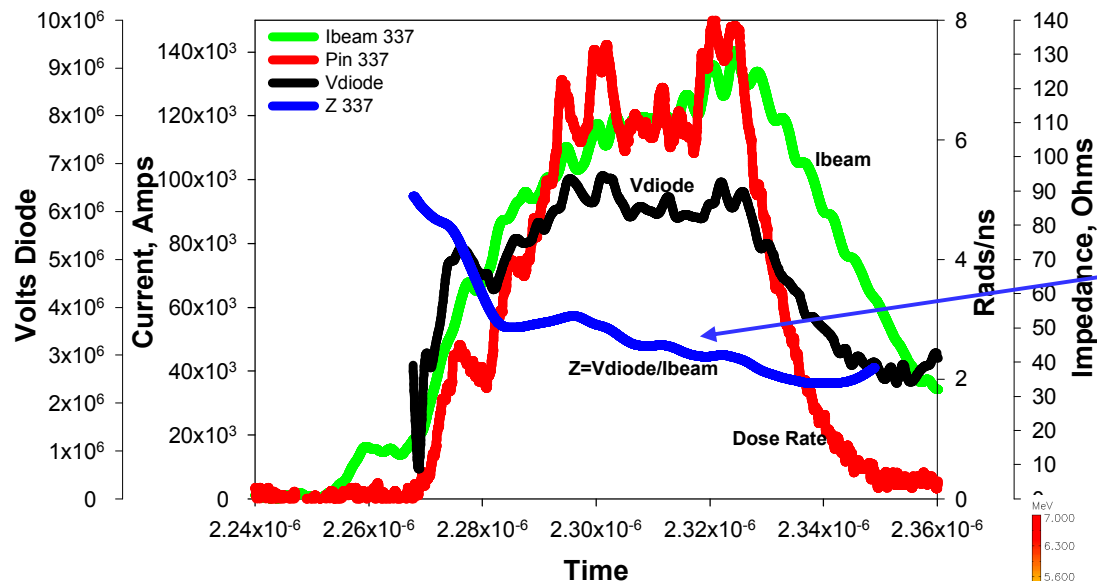
Spot and dose



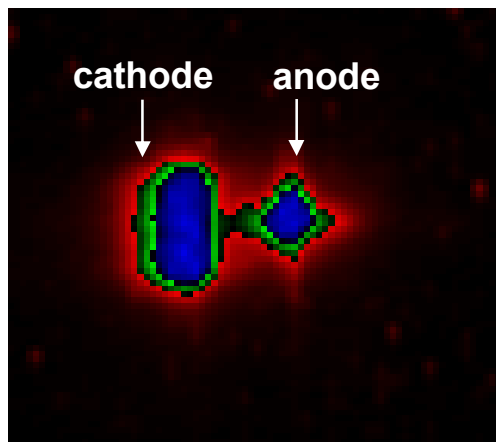
Small cathode produces 150 rad@m, 1.85mm spot



Plasma gap closure must be controlled for brighter performance on the SMP

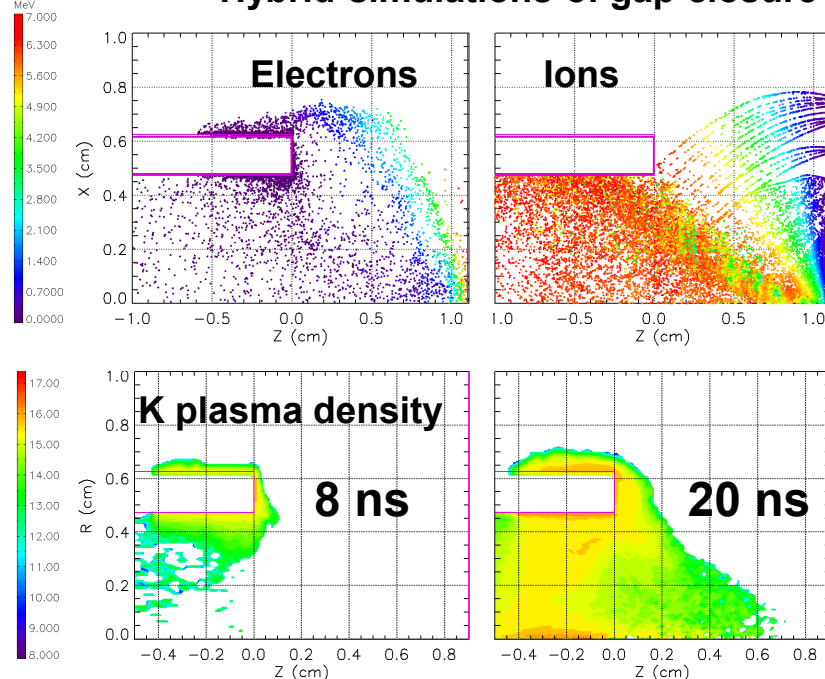


Diode impedance decreases during pulse



Light emission in A-K gap

Hybrid simulations of gap closure



Future driver architectures: 1-MV Radiographic system based on LTD's

A 1-MV, 140 kA radiographic Linear Transformer Driver (LTD) has been assembled and tested in Russia and now at Sandia

Voltage adds along coaxial Magnetically insulated transmission line, like an IVA

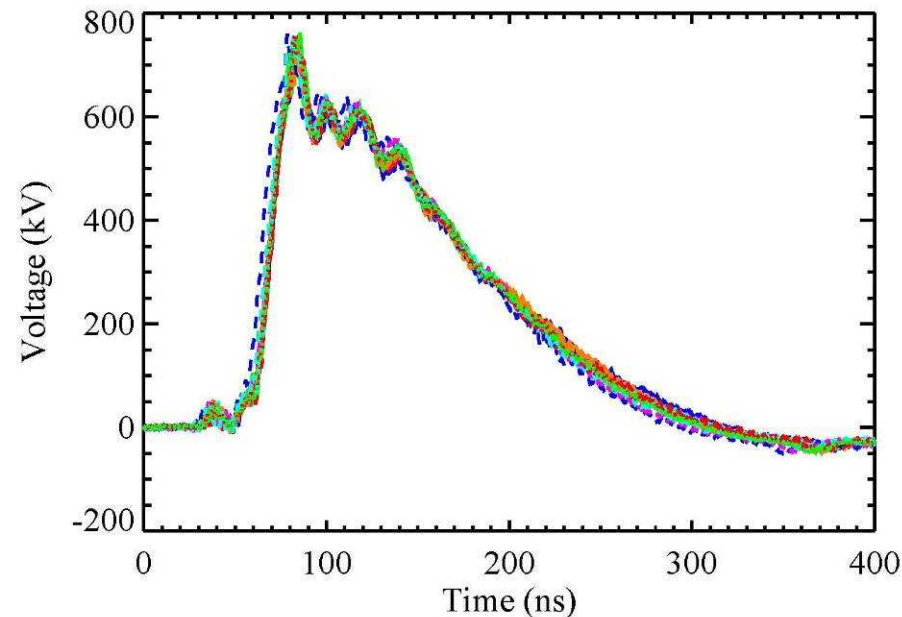
Successfully tested with electron-beam diode load for more than 300 shots



Advantages: lower cost and smaller foot-print:

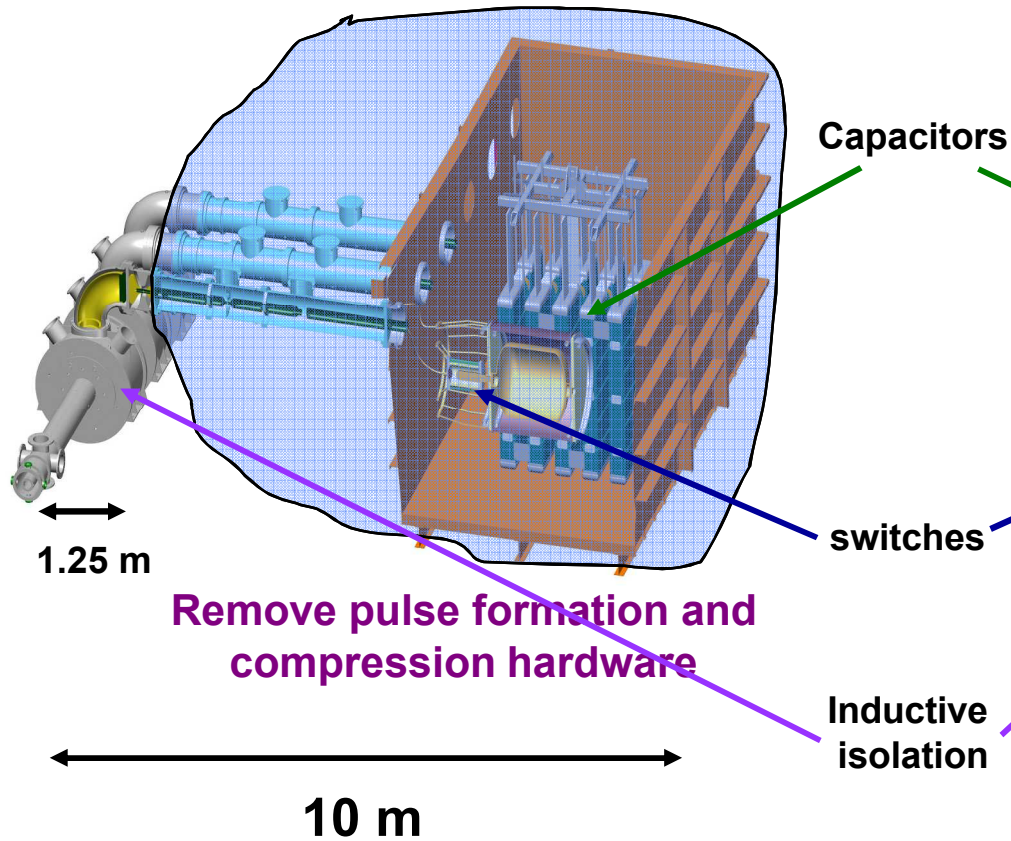
Status: Demonstrated both single and stacked-cavity performance to 1 MV.

Collaborators: designed and built in collaboration with Institute of High Current Electronics in Tomsk, Russia and CEA and ITHPP in France.

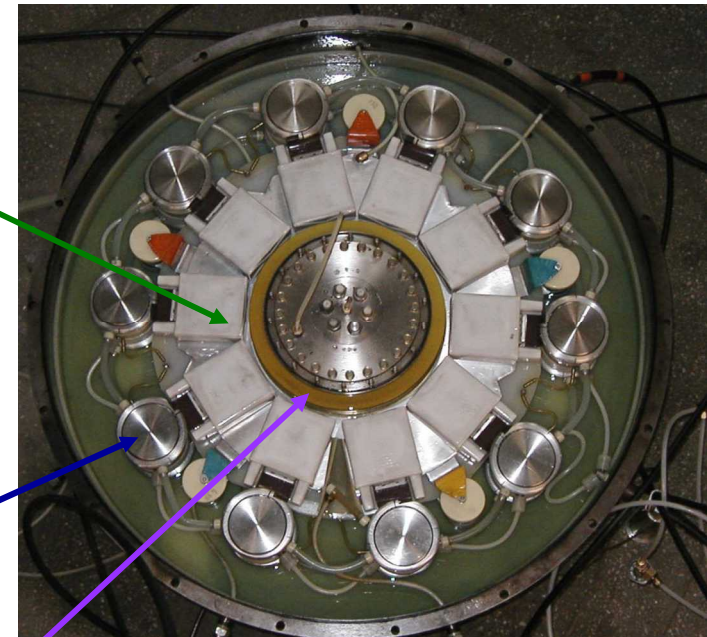


The LTD is much more compact than conventional IVAs

Inductive Voltage Adder (IVA)



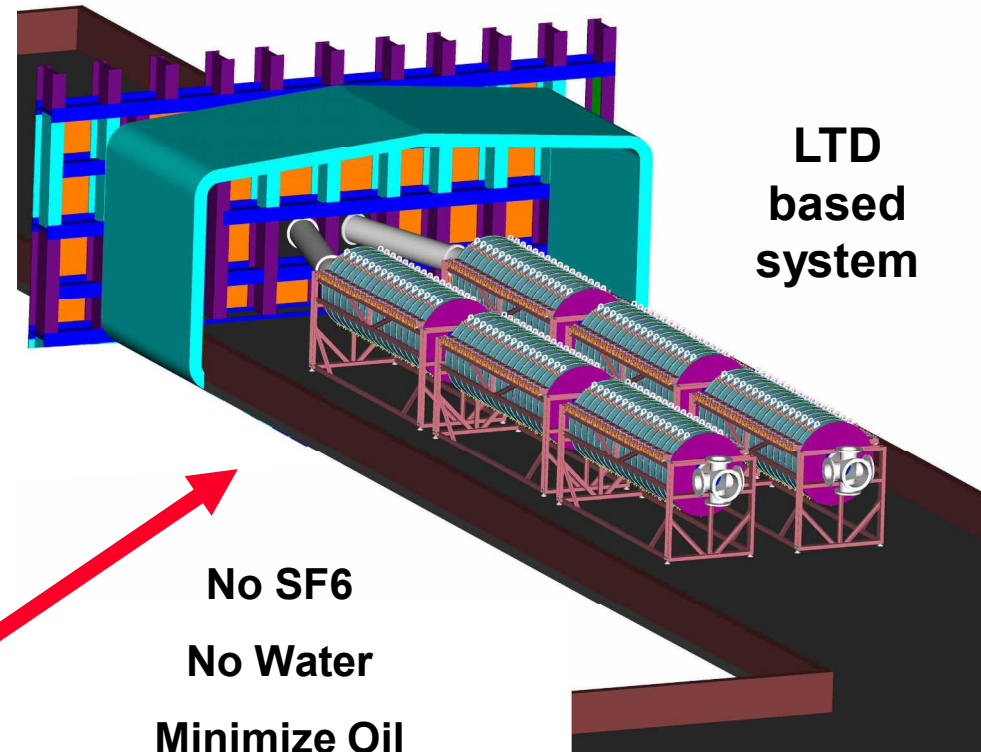
Linear Transformer Driver (LTD)





A 2-axis LTD can provide 6.5 MV, 250 rad@m, 2.5mm spot in same foot print as Cygnus system

12' wide x 50' long x 6' high
Can replicate existing Cygnus capability
As well as provide increased capability
in steps up to 250 rad@m, 2.5-mm spot



No SF6
No Water
Minimize Oil
Closed geometry

Cygnus

**Use either an SMP or negative
polarity Rod-pinch diode at ~ 50
Ohms to drive 6.5 MeV, 130 kA
diode.**